

METHOD OF MANUFACTURING FLASH MEMORY DEVICE

ABSTRACT OF THE DISCLOSURE

5 The present invention relates a method of manufacturing a flash
memory device. In case of forming a dielectric film consisting of a lower
oxide film, a nitride film and upper oxide film that is formed between a
floating gate and a control gate, a nitrification process is performed after the
lower oxide film is formed, thus forming a nitrogen layer below the lower
10 oxide film. Then, an annealing process using an oxygen gas is performed to
move the nitrogen layer onto the surface of the lower oxide film, thus forming
a nitride film. Therefore, the present invention can reduce the effective
thickness of the dielectric film.